AOTF10B60D

600V, 10A Alpha IGBT™ with Diode

General Description

The Alpha IGBT™ line of products offers best-in-class performance in conduction and switching losses, with robust short circuit capability. They are designed for ease of paralleling, minimal gate spike under high dV/dt conditions and resistance to oscillations. The soft co-package diode is targeted for minimal losses in motor control applications.

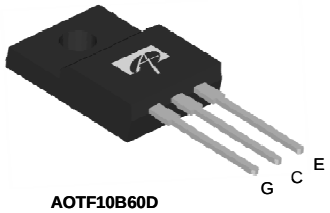
Product Summary

V_{CE}	600V
I_C (T_C=100℃)	10A
$V_{CE(sat)}$ (T_C=25℃)	1.53V

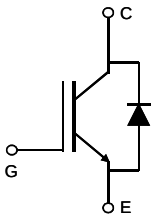
RoHS Compliant

Top View

TO-220F



AOTF10B60D



Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	AOTF10B60D	Units
Collector-Emitter Voltage		V_{CE}	600	V
Gate-Emitter Voltage		V_{GE}	±20	V
Continuous Collector Current	T_C=25℃	I_C	20$	A
	T_C=100℃		10$	
Pulsed Collector Current, Limited by T_{Jmax}		I_{CM}	40	A
Turn off SOA, V_{CE} ⩽ 600V, Limited by T_{Jmax}		I_{LM}	40	A
Continuous Diode Forward Current	T_C=25℃	I_F	20	A
	T_C=100℃		10	
Diode Pulsed Current, Limited by T_{Jmax}		I_{FM}	40	A
Short circuit withstanding time V_{GE} = 15V, V_{CE} ⩽ 400V, Delay between short circuits ⩾ 1.0s, T_C=150℃		t_{SC}	10	µs
Power Dissipation	T_C=25℃	P_D	42	W
	T_C=100℃		16.7	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	℃
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300	℃

Thermal Characteristics

Parameter	Symbol	AOTF10B60D	Units
Maximum Junction-to-Ambient	$R_{\theta JA}$	65	℃/W
Maximum IGBT Junction-to-Case	$R_{\theta JC}$	3	℃/W
Maximum Diode Junction-to-Case	$R_{\theta JC}$	4	℃/W

$:TO220F I_C Follow TO220

Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{CES}	Collector-Emitter Breakdown Voltage	I_C=1mA, V_{GE}=0V, T_J=25℃		600	-	-	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{GE}=15V, I_C=10A	T_J=25℃	-	1.53	1.8	V
			T_J=125℃	-	1.75	-	
			T_J=150℃	-	1.81	-	
V_F	Diode Forward Voltage	V_{GE}=0V, I_C=10A	T_J=25℃	-	1.52	1.85	V
			T_J=125℃	-	1.48	-	
			T_J=150℃	-	1.44	-	
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	V_{CE}=V_{GE}, I_C=1mA		-	5.8	-	V
I_{CES}	Zero Gate Voltage Collector Current	V_{CE}=600V, V_{GE}=0V	T_J=25℃	-	-	10	μA
			T_J=125℃	-	-	200	
			T_J=150℃	-	-	1000	
I_{GES}	Gate-Emitter leakage current	V_{CE}=0V, V_{GE}=±20V		-	-	±100	nA
g_{FS}	Forward Transconductance	V_{CE}=20V, I_C=10A		-	4.8	-	S
DYNAMIC PARAMETERS							
C_{ies}	Input Capacitance	V_{GE}=0V, V_{CE}=25V, f=1MHz		-	824	-	pF
C_{oes}	Output Capacitance			-	68	-	pF
C_{res}	Reverse Transfer Capacitance			-	2.7	-	pF
Q_g	Total Gate Charge	V_{GE}=15V, V_{CE}=480V, I_C=10A		-	17.4	-	nC
Q_{ge}	Gate to Emitter Charge			-	6.2	-	nC
Q_{gc}	Gate to Collector Charge			-	6.3	-	nC
$I_{C(SC)}$	Short circuit collector current, Max. 1000 short circuits, Delay between short circuits ⩾ 1.0s	V_{GE}=15V, V_{CE}=400V, R_G=30Ω		-	43	-	A
R_g	Gate resistance	V_{GE}=0V, V_{CE}=0V, f=1MHz		-	3.2	-	Ω
SWITCHING PARAMETERS, (Load Iductive, T_J=25℃)							
$t_{D(on)}$	Turn-On DelayTime	T_J=25℃ V_{GE}=15V, V_{CE}=400V, I_C=10A, R_G=30Ω, Parasitic Inductance=100nH		-	10	-	ns
t_r	Turn-On Rise Time			-	15	-	ns
$t_{D(off)}$	Turn-Off Delay Time			-	72	-	ns
t_f	Turn-Off Fall Time			-	8.8	-	ns
E_{on}	Turn-On Energy			-	0.26	-	mJ
E_{off}	Turn-Off Energy			-	0.07	-	mJ
E_{total}	Total Switching Energy			-	0.33	-	mJ
t_{rr}	Diode Reverse Recovery Time	T_J=25℃ I_F=10A,dI/dt=200A/μs,V_{CE}=400V		-	105	-	ns
Q_{rr}	Diode Reverse Recovery Charge			-	0.25	-	μC
I_{rm}	Diode Peak Reverse Recovery Current			-	5	-	A
SWITCHING PARAMETERS, (Load Iductive, T_J=150℃)							
$t_{D(on)}$	Turn-On DelayTime	T_J=150℃ V_{GE}=15V, V_{CE}=400V, I_C=10A, R_G=30Ω, Parasitic Inductance=100nH		-	10.4	-	ns
t_r	Turn-On Rise Time			-	15.6	-	ns
$t_{D(off)}$	Turn-Off Delay Time			-	91	-	ns
t_f	Turn-Off Fall Time			-	10.4	-	ns
E_{on}	Turn-On Energy			-	0.35	-	mJ
E_{off}	Turn-Off Energy			-	0.16	-	mJ
E_{total}	Total Switching Energy			-	0.51	-	mJ
t_{rr}	Diode Reverse Recovery Time	T_J=150℃ I_F=10A,dI/dt=200A/μs,V_{CE}=400V		-	194	-	ns
Q_{rr}	Diode Reverse Recovery Charge			-	0.55	-	μC
I_{rm}	Diode Peak Reverse Recovery Current			-	6.3	-	A

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

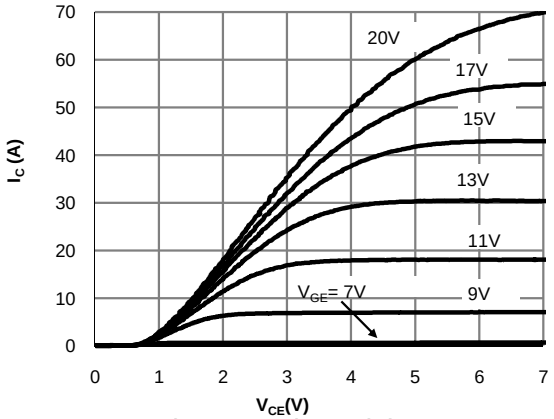


Fig 1: Output Characteristic (T_j=25℃)

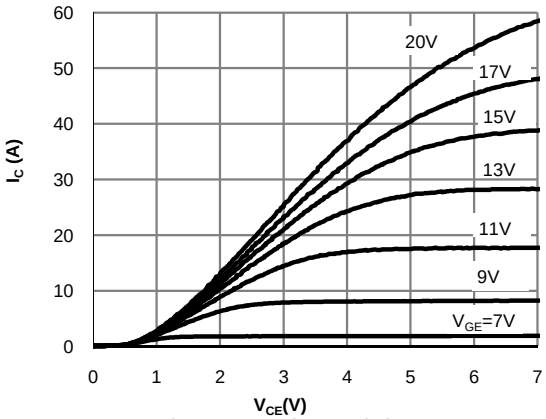


Fig 2: Output Characteristic (T_j=150℃)

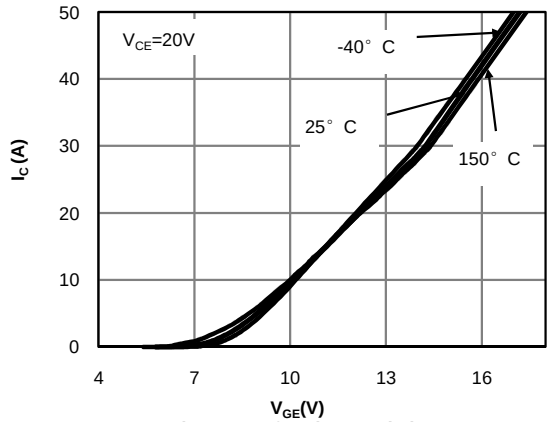


Fig 3: Transfer Characteristic

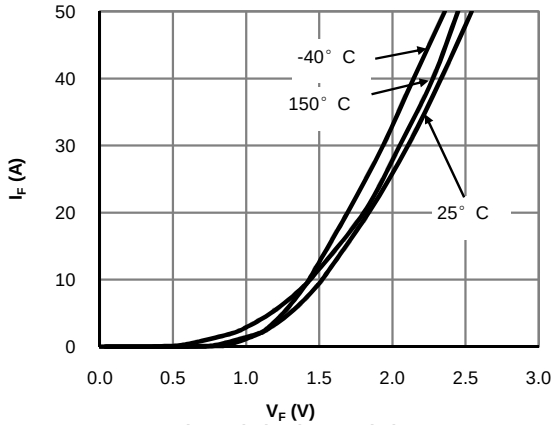


Fig 4: Diode Characteristic

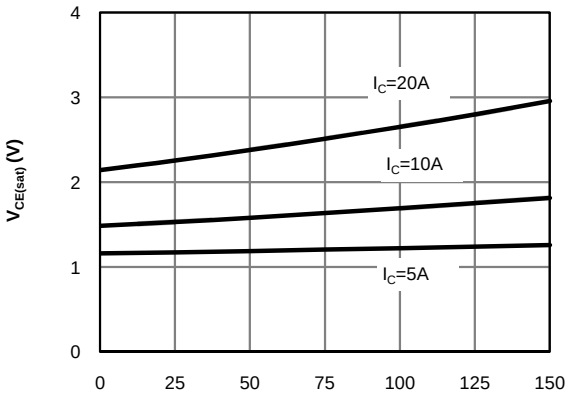


Fig 5: Collector-Emitter Saturation Voltage vs. Junction Temperature

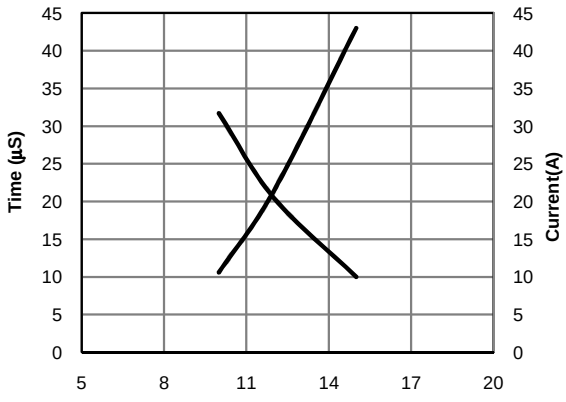


Fig 6: V_{GE} vs. Short Circuit Time (V_{CE}=400V,T_C=25℃)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

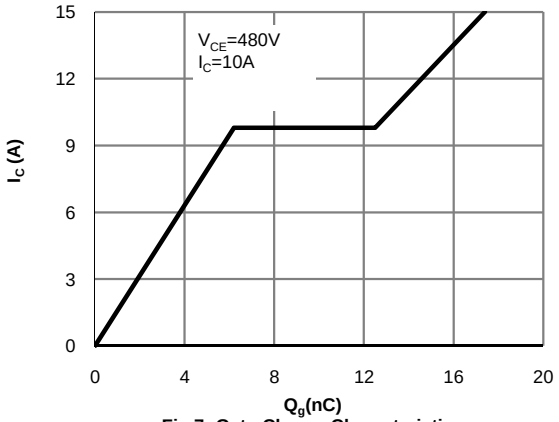


Fig 7: Gate-Charge Characteristics

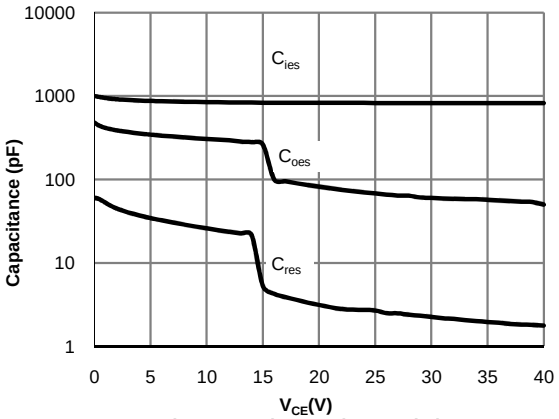


Fig 8: Capacitance Characteristic

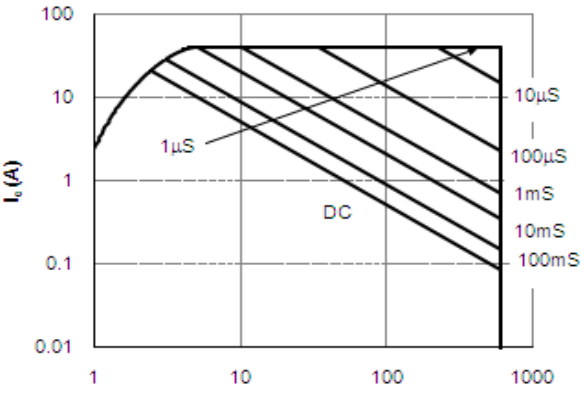


Fig 9: Forward Bias Safe Operating Area
(T_C=25C,V_{GE}=15V)

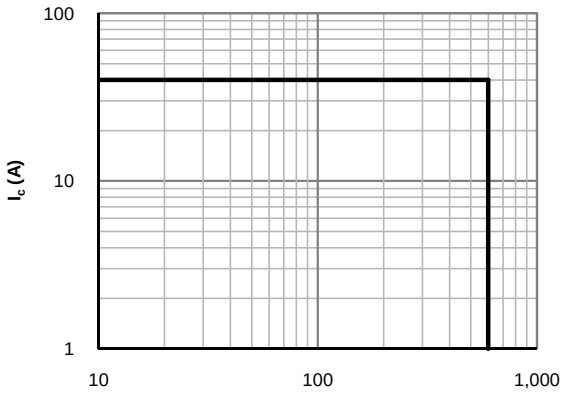


Fig 10: Reverse Bias SOA
(T_j=150℃,V_{GE}=15V)

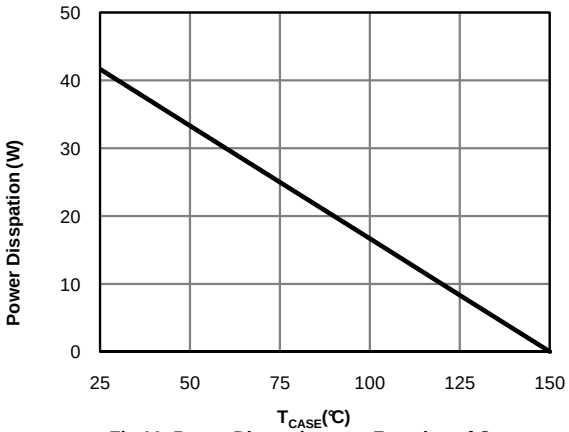


Fig 11: Power Disspation as a Function of Case

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

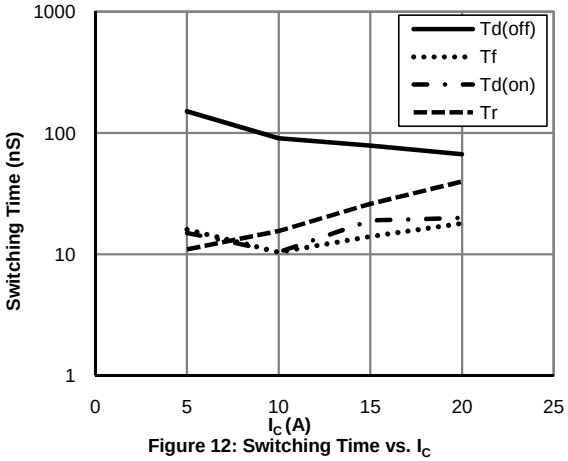


Figure 12: Switching Time vs. I_C
(T_j=150℃,V_{GE}=15V,V_{CE}=400V,R_g=30Ω)

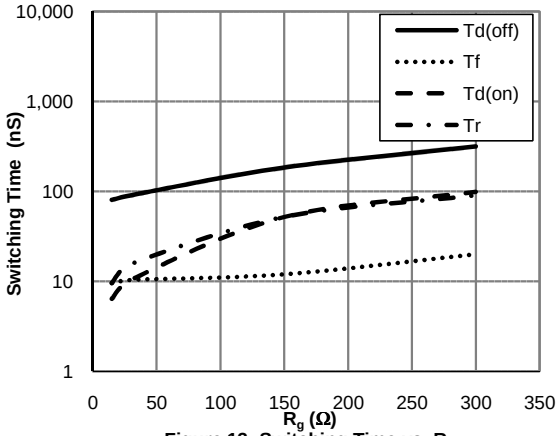


Figure 13: Switching Time vs. R_g
(T_j=150℃,V_{GE}=15V,V_{CE}=400V,I_C=10A)

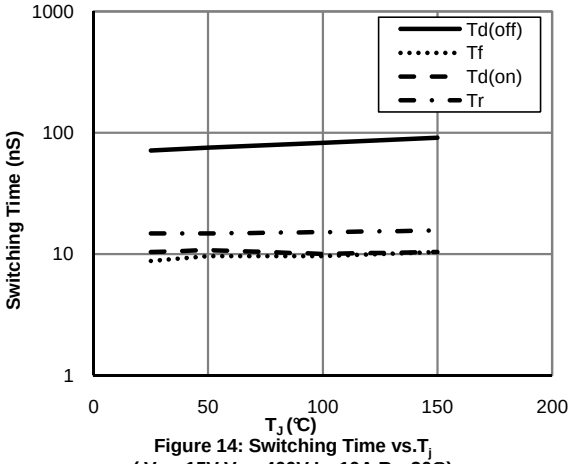


Figure 14: Switching Time vs.T_j
(V_{GE}=15V,V_{CE}=400V,I_C=10A,R_g=30Ω)

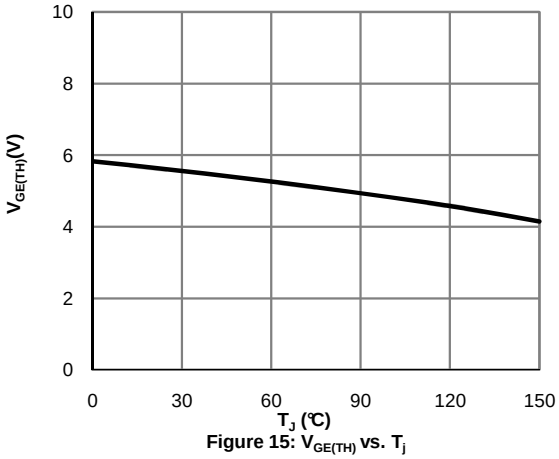


Figure 15: $V_{GE(TH)}$ vs. T_j

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

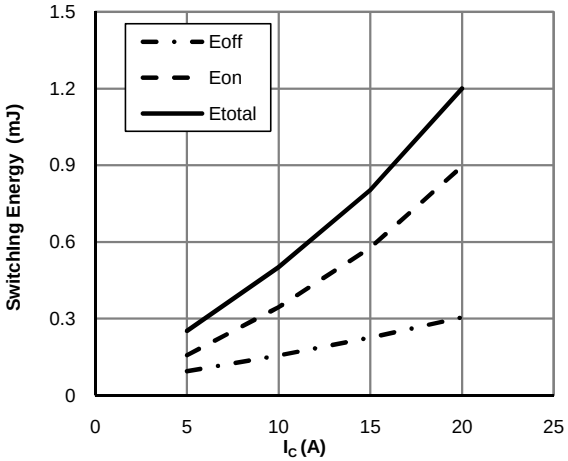


Figure 16: Switching Loss vs. I_C
(T_j=150℃,V_{GE}=15V,V_{CE}=400V,R_g=30Ω)

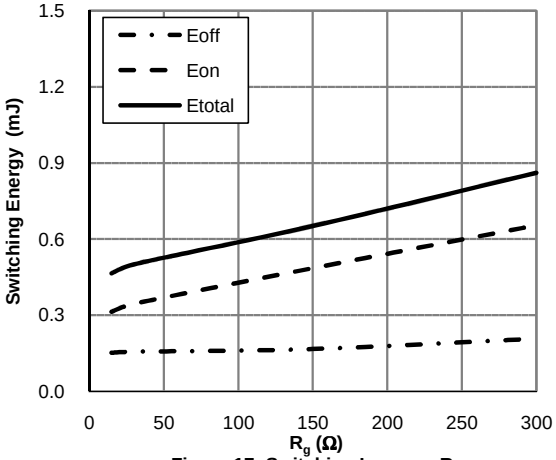


Figure 17: Switching Loss vs. R_g
(T_j=150℃,V_{GE}=15V,V_{CE}=400V,I_C=10A)

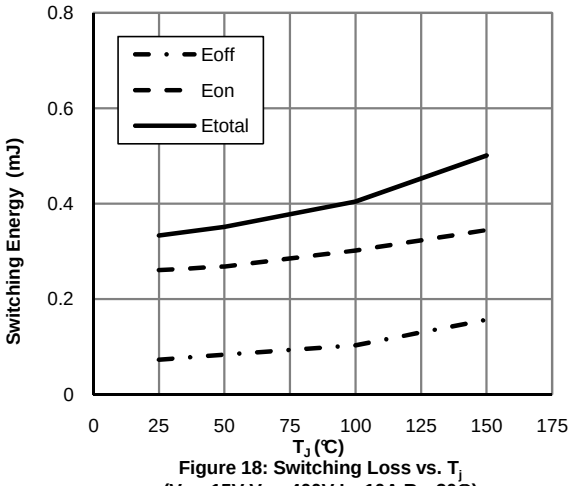


Figure 18: Switching Loss vs. T_j
(V_{GE}=15V,V_{CE}=400V,I_C=10A,R_g=30Ω)

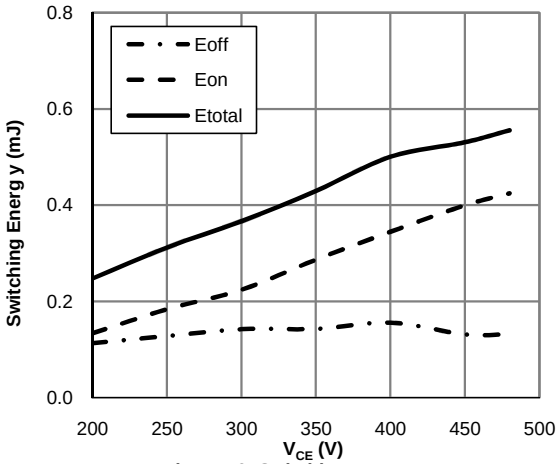


Figure 19: Switching Loss vs. V_{CE}
(T_j=150℃,V_{GE}=15V,I_C=10A,R_g=30Ω)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

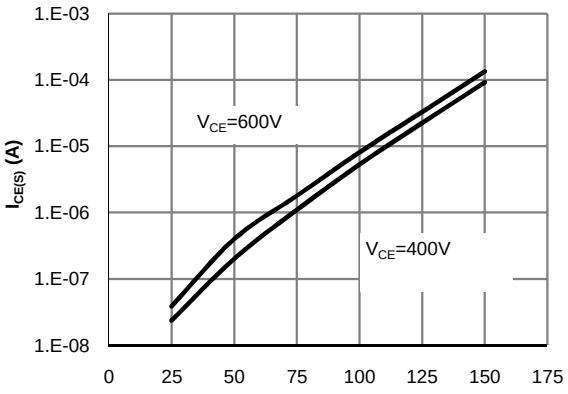


Fig 20: Diode Reverse Leakage Current vs. Junction Temperature

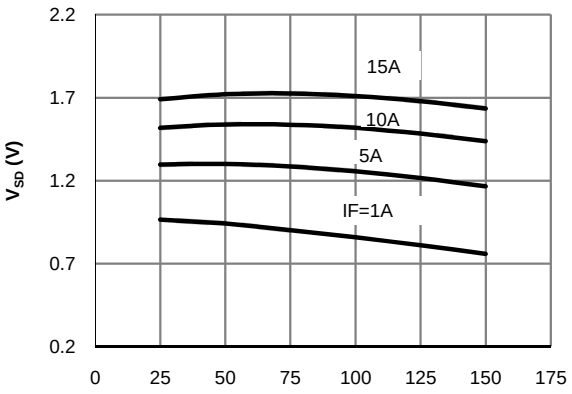


Fig 21: Diode Forward voltage vs. Junction Temperature

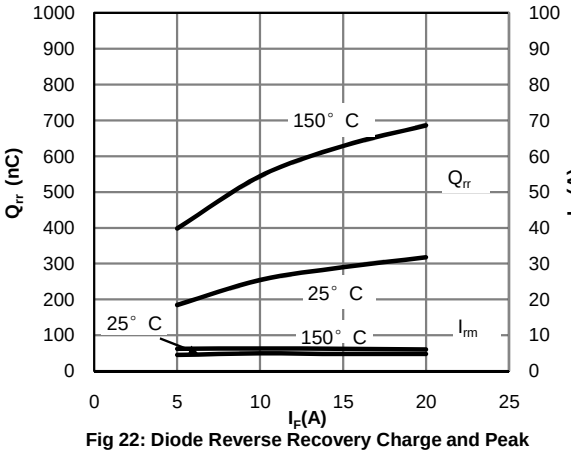


Fig 22: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current (V_{GE}=15V,V_{CE}=400V, di/dt=200A/µs)

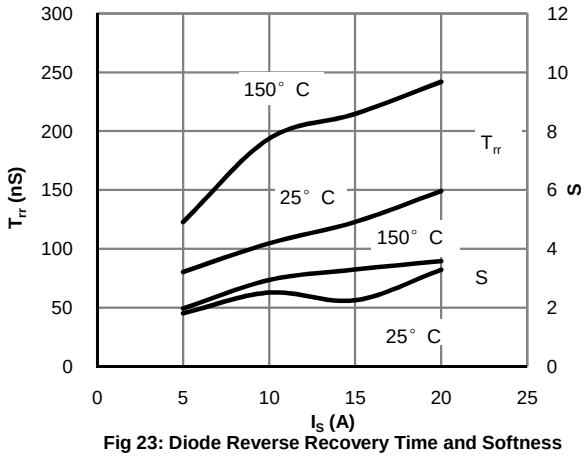


Fig 23: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current (V_{GE}=15V,V_{CE}=400V, di/dt=200A/µs)

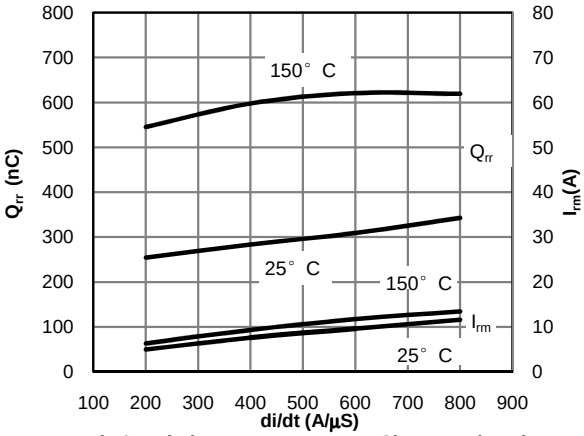


Fig 24: Diode Reverse Recovery Charge and Peak Current vs. di/dt (V_{GE}=15V,V_{CE}=400V,I_F=10A)

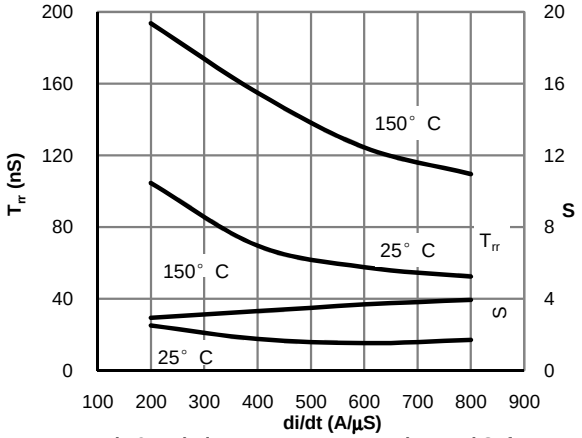


Fig 25: Diode Reverse Recovery Time and Softness Factor vs. di/dt (V_{GE}=15V,V_{CE}=400V,I_F=10A)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

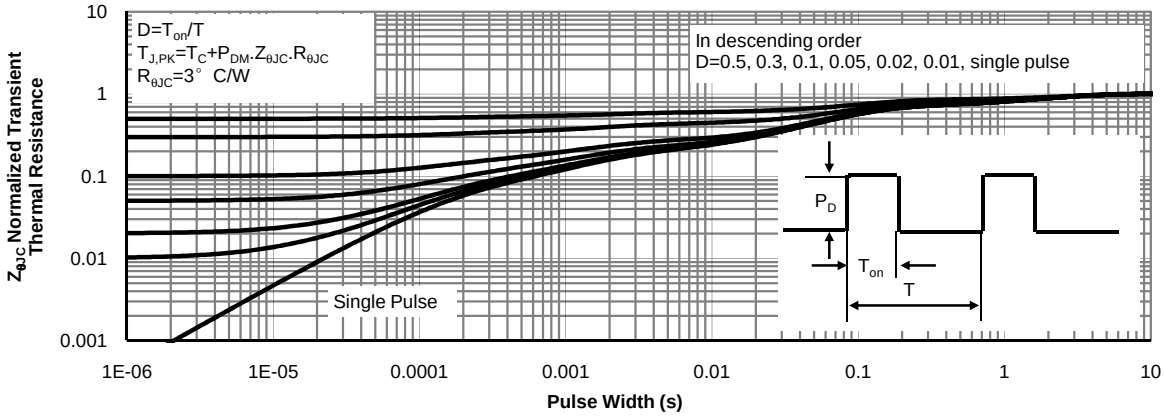


Figure 26: Normalized Maximum Transient Thermal Impedance for IGBT

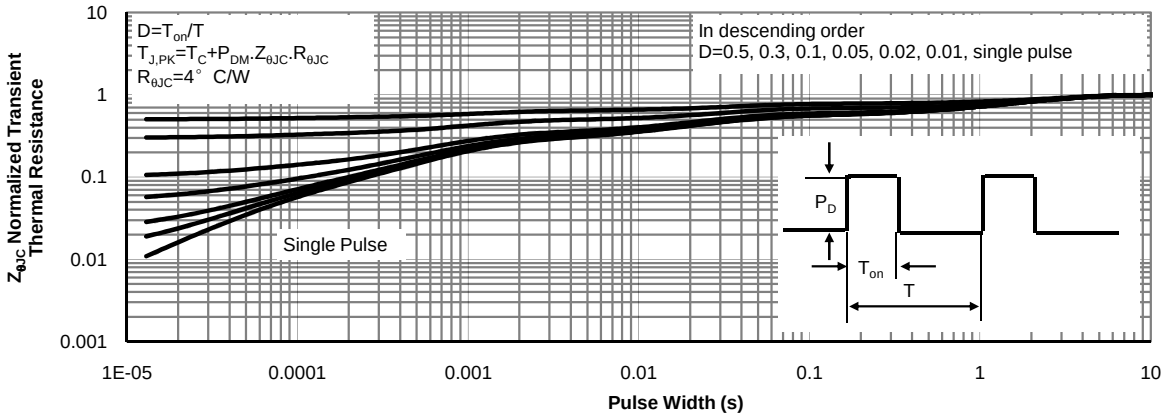
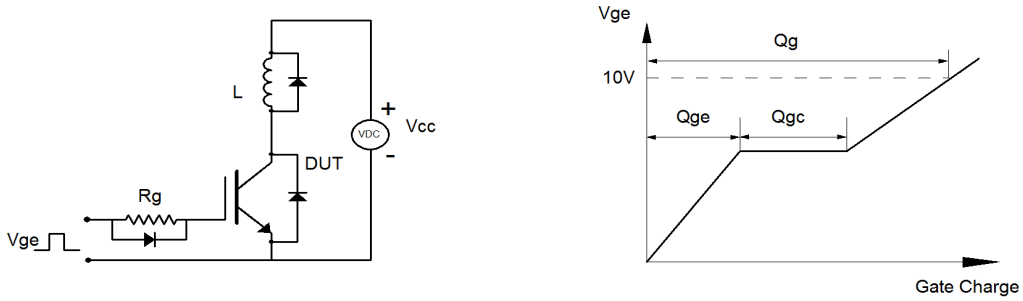
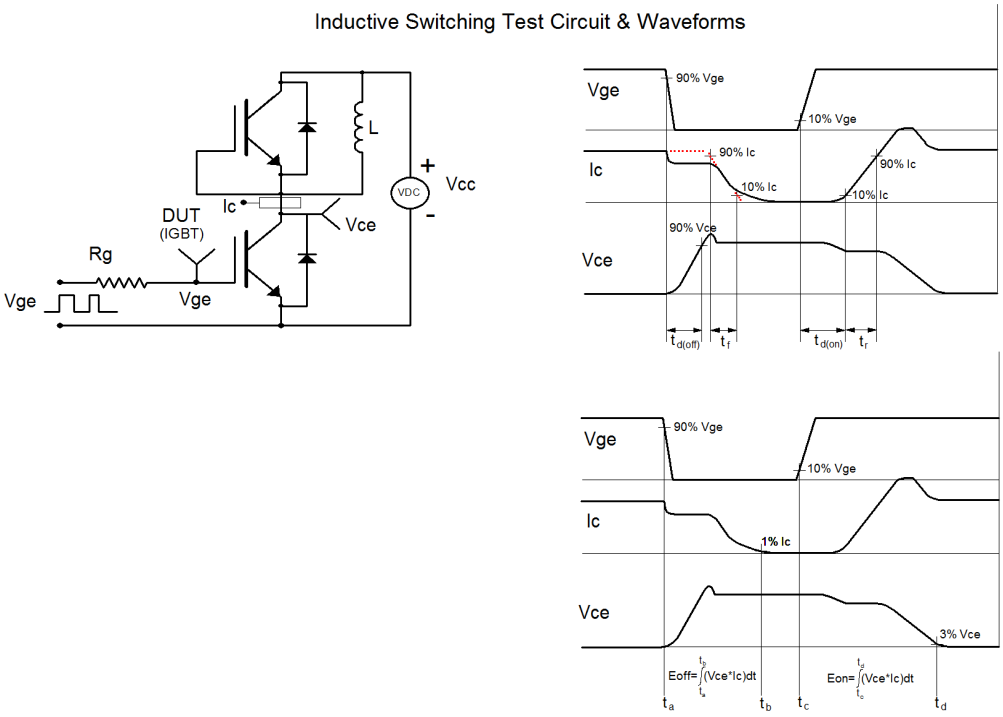


Figure 27: Normalized Maximum Transient Thermal Impedance for Diode

Gate Charge Test Circuit & Waveform



Inductive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms